

# RB521S-30

## SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

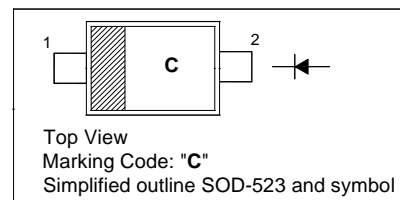
for low current rectification and high speed switching applications

### Features

- Extremely small surface mounting type

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



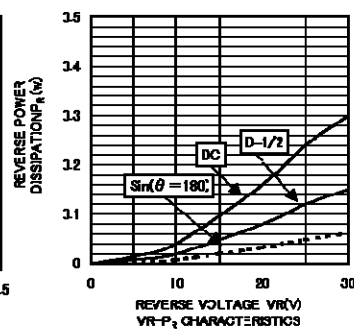
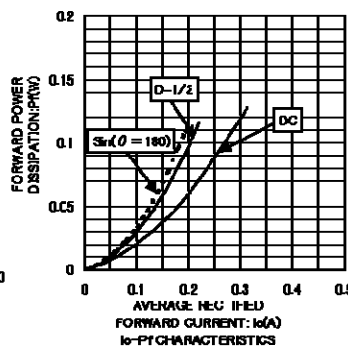
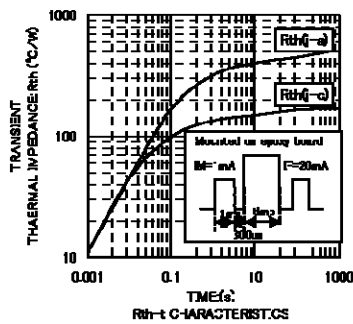
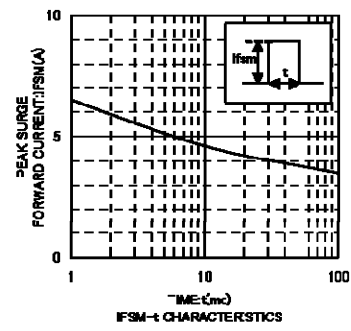
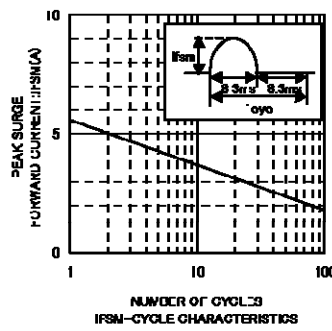
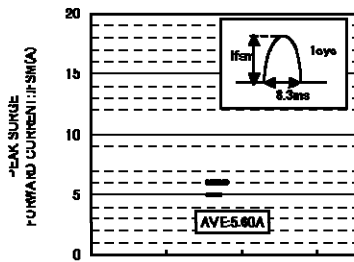
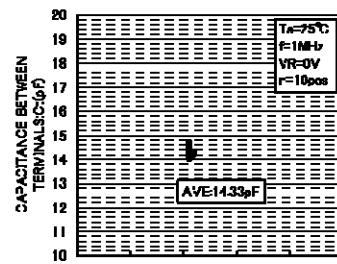
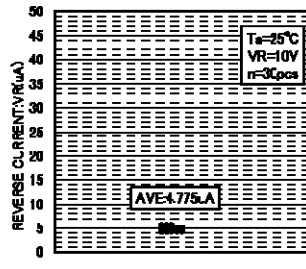
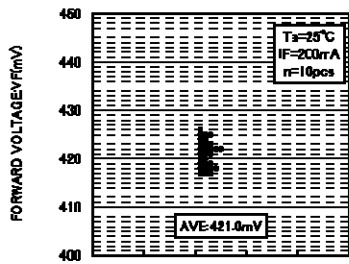
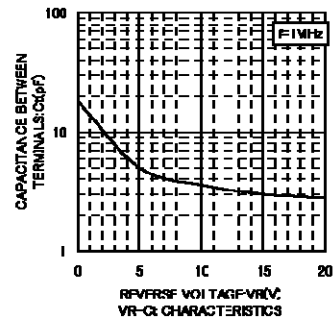
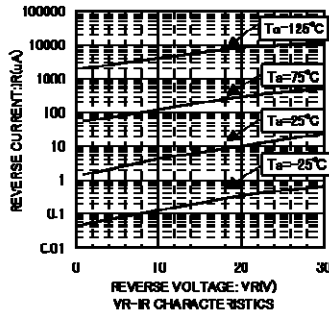
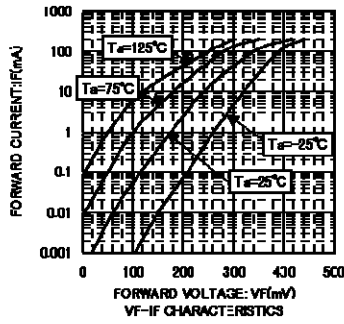
### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Mean Rectifying Current	$I_O$	200	mA
Peak Forward Surge Current (60Hz for Cyc.)	$I_{FSM}$	1	A
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 40 to + 125	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	$V_F$	0.5	V
Reverse Current at $V_R = 10\text{ V}$	$I_R$	30	$\mu\text{A}$

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## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523

